



Extracting information from partially depleted Si detectors with digital sampling electronics

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AIM:
 Study of the performances (identification and energy measurement) of an underdepleted silicon detector. Five different bias voltages have been used, one corresponding to full depletion (used as a reference for comparison), the other ones associated with a depleted layer from 90% to 60% of the total detector thickness. [1]

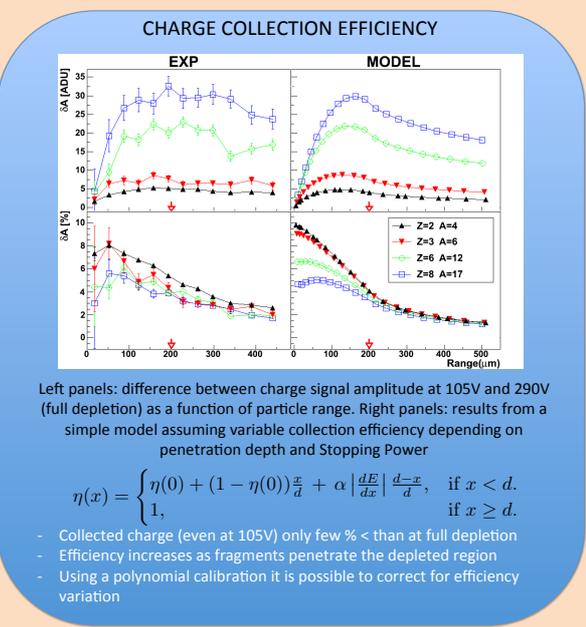
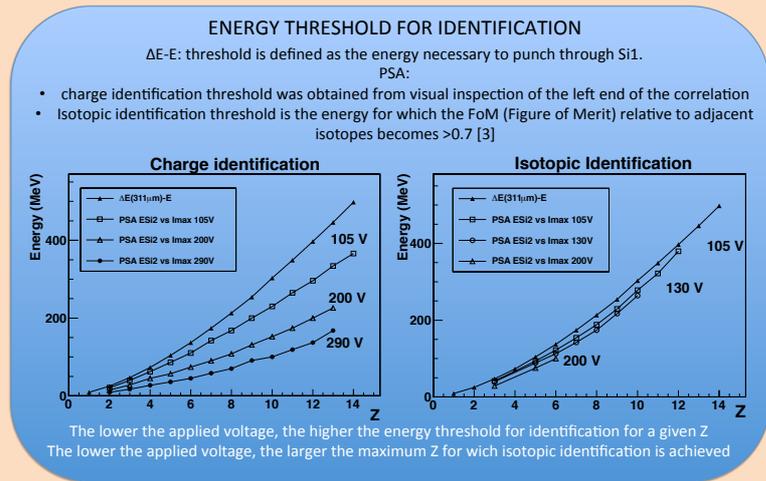
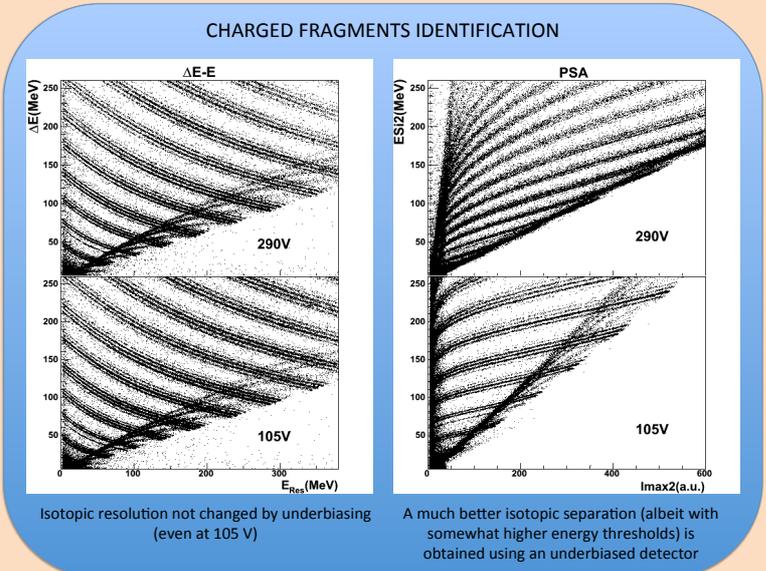
MEASUREMENT SETUP

- Si1 310μm thickness, Si2 511μm thickness and Cs(Tl) ~10cm thickness
- Si detectors reverse mounted to improve PSA identification [2]
- Current and charge signals separately digitized by dedicated ADC [3]
- Si detector cut at 7° with respect to crystalline planes or axes to avoid channeling [4]

Si1 bias voltage: fixed at 140V (slightly above depletion)
 Si2 bias voltage: five different values have been tested (105, 130, 200, 235, 290 V)

V _{bias} (V)	d (μm)	Max RiseTime (20-70%)(μs)
105	200	13
130	170	10
200	90	3
235	50	1.5
290	0	0.45

Underbiased detector requires long collection time
 Our results were achieved using relatively long acquired signals (~70μs) and shaping time (~50μs)



CONCLUSIONS

- High charge collection efficiency:
 - For 60% depletion, less than 10% of the total charge is lost for short range fragments
 - Collection efficiency for punching through fragments ~97-98%
- ΔE-E identification not affected by underbias, even for 60% depletion
- PSA identification:
 - Isotopic identification improves with underbias (identification not even possible at full depletion due to doping non-uniformity of about ~6% [5])
 - Energy thresholds for Z identification via PSA increase with underbias

[1] G. Pasquali *et al* (FAZIA Collaboration), *accepted for publication on Eur. Phys. J A*
 [2] N. Le Neindre *et al* (FAZIA Collaboration), *Nucl. Instr. And Meth. A* **701**, 145 (2013)
 [3] R. Bougault *et al* (FAZIA Collaboration) *Eur. Phys. J A* **50**, 47 (2014)
 [4] L. Bardelli *et al* (FAZIA Collaboration), *Nucl. Instr. And Meth. A* **654**, 272 (2011)
 [5] S. Carboni *et al* (FAZIA Collaboration), *Nucl. Instr. And Meth. A* **664**, 251 (2012)